Abstracts

Microwave GaAs FET Switching

R.A. Gaspari and H.H. Yee. "Microwave GaAs FET Switching." 1978 MTT-S International Microwave Symposium Digest 78.1 (1978 [MWSYM]): 58-60.

Microwave switching using GaAs field effect transistors offers very high speed and low drive control power. Using arrays of such FETs, an 8 x 8 switch matrix was constructed for 4 GHz SS-TDMA spacecraft applications which achieved 1 ns transition time at 10 mW drive control power. Matrix isolation over 500 MHz bandwidth was 50 dB.

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